Electronic Supplementary Material (ESI) for RSC Advances.

Supporting Information:

A Facile One-step Route to Synthesize Three-layer Nanostructure of CuS/RGO/Ni_3S_2 and its High Electrochemical Performance

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Table S1. Charging, discharging capacitances and the corresponding coulombic efficiencies for CRNS-180-24 at various current densities.

Current density (mA cm^{-2})	40	60	80	100	150	200
Charging capacitance (mF cm^{-2})	10603.6	9501.8	8334.5	6581.8	6109.1	5236.4
Discharging capacitance (mF cm^{-2})	10494.5	9016.4	7979.6	6356.4	5694.5	4930.9
Coulombic efficiency	98.97%	94.89%	95.74%	96.58%	93.21%	94.17%

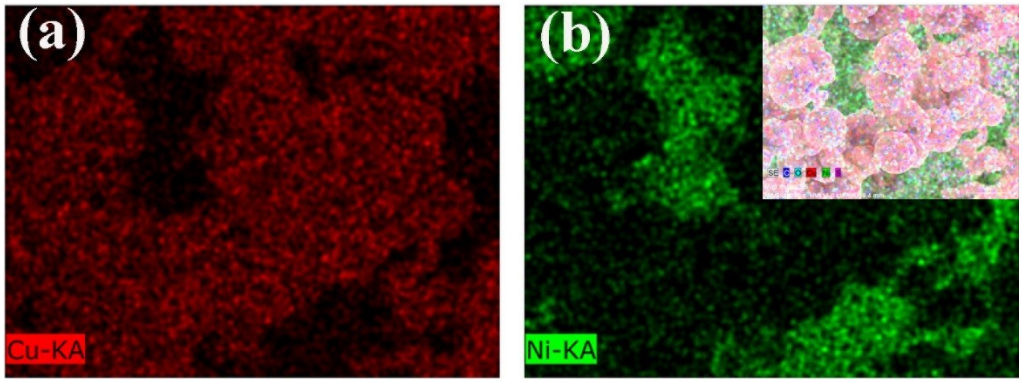

Fig. S1 EDS mapping of CRNS composite with big sphere blocks: (a) Cu elements (red); (b) Ni elements (green) and (b inset) corresponding overlay of C, O, Cu, Ni and S elements.

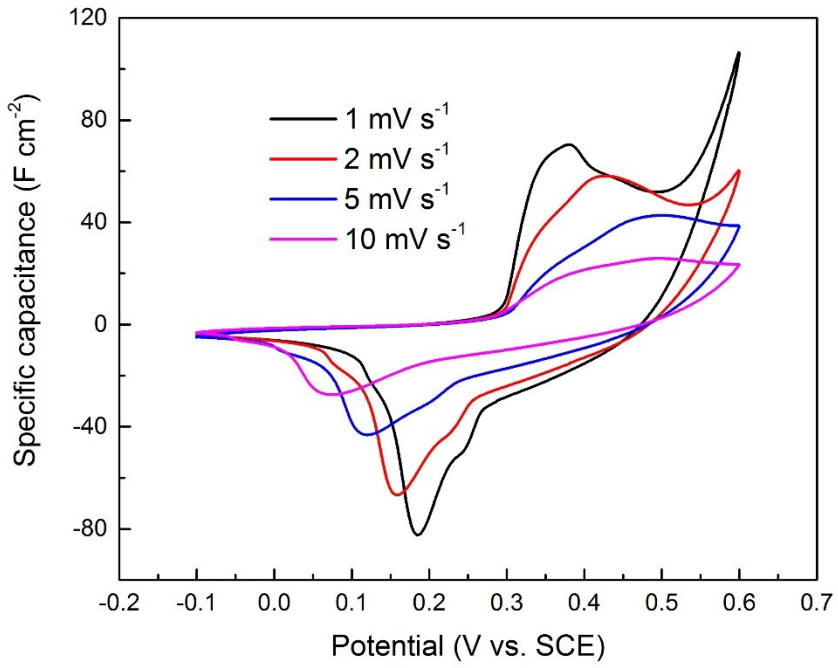

Fig. S2 Cyclic voltammetry curves expressed as specific capacitance vs. cell potential for CRNS-180-24 at various scan rates.